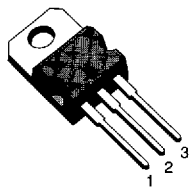
SGS-THOMSON MICROELECTRONICS

STP5N60
STP5N60FI

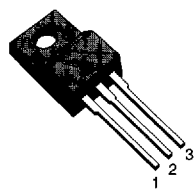
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STP5N60	600 V	< 1.6 Ω	5.6 A
STP5N60FI	600 V	< 1.6 Ω	3.2 A

- TYPICAL $R_{DS(on)}$ = 1.33 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- APPLICATION ORIENTED CHARACTERIZATION



TO-220

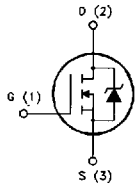


ISOWATT220

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- CHOPPER REGULATORS, CONVERTERS, MOTOR CONTROL, LIGHTING FOR INDUSTRIAL AND CONSUMER ENVIRONMENT

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP5N60	STP5N60FI	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	600		V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	600		V
V_{GS}	Gate-source Voltage	± 20		V
I_D	Drain Current (continuous) at T_c = 25 °C	5.6	3.2	A
I_D	Drain Current (continuous) at T_c = 100 °C	3.5	2	A
I_{DM}(•)	Drain Current (pulsed)	20	20	A
P_{tot}	Total Dissipation at T_c = 25 °C	100	40	W
	Derating Factor	1	0.32	W/°C
V_{ISO}	Insulation Withstand Voltage (DC)	—	2000	V
T_{stg}	Storage Temperature	-65 to 150		°C
T_j	Max. Operating Junction Temperature	150		°C

(•) Pulse width limited by safe operating area

THERMAL DATA

			TO-220	ISOWATT220	
$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	1	3.12	°C/W
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	62.5		°C/W
$R_{thc\text{-}sink}$	Thermal Resistance Case-sink	Typ	0.5		°C/W
T_l	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	5.6	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25$ °C, $I_D = I_{AR}$, $V_{DD} = 50$ V)	350	mJ
E_{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$)	15	mJ
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive ($T_c = 100$ °C, pulse width limited by T_j max, $\delta < 1\%$)	3.5	A

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250$ µA $V_{GS} = 0$	600			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	V_{DS} = Max Rating V_{DS} = Max Rating x 0.8 $T_c = 125$ °C			250 1000	µA µA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20$ V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250$ µA	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10$V $I_D = 2.5$ A $V_{GS} = 10$V $I_D = 2.5$ A $T_c = 100$°C		1.33	1.5 3	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10$ V	5.6			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 2.5$ A	1.5	3.4		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25$ V $f = 1$ MHz $V_{GS} = 0$		720 120 50	1000 170 70	pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 300 V I_D = 2.5 A R_G = 50 Ω V_{GS} = 10 V (see test circuit, figure 3)		55 150	75 200	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	V_{DD} = 480 V I_D = 5 A R_G = 50 Ω V_{GS} = 10 V (see test circuit, figure 5)		115		A/µs
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 480 V I_D = 5 A V_{GS} = 10 V		46 8 25	65	nC nC nC

SWITCHING OFF

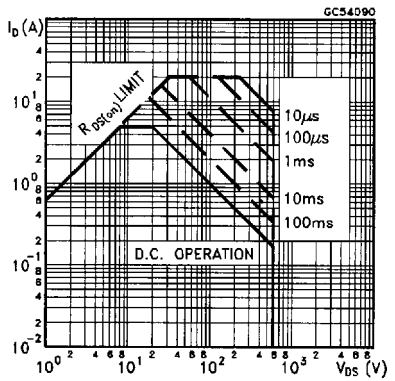
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 480 V I_D = 5 A R_G = 50 Ω V_{GS} = 10 V (see test circuit, figure 5)		80 25 120	105 35 160	ns ns ns

SOURCE DRAIN DIODE

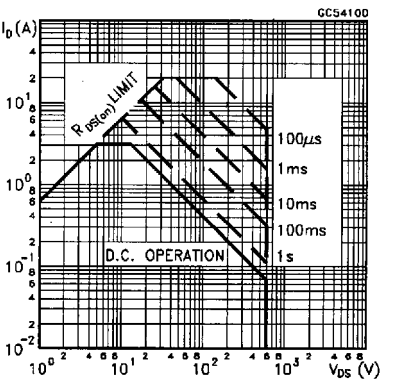
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				5.6 20	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 5.9 A V_{GS} = 0			2	V
t_{rr}	Reverse Recovery Time	I_{SD} = 6 A di/dt = 100 A/µs V_{DD} = 100 V T_j = 150 °C		525		ns
Q_{rr}	Reverse Recovery Charge	(see test circuit, figure 5)		5.8		µC
I_{RRM}	Reverse Recovery Current			22		A

(*) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %
(•) Pulse width limited by safe operating area

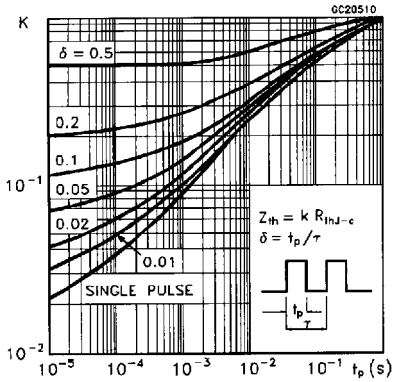
Safe Operating Areas For TO-220



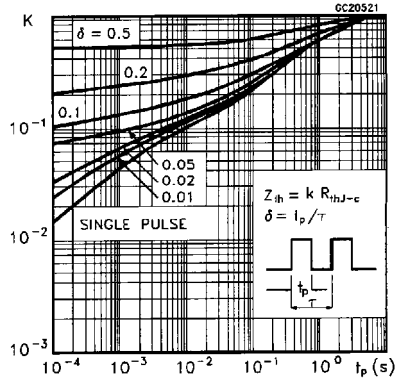
Safe Operating Areas For ISOWATT220



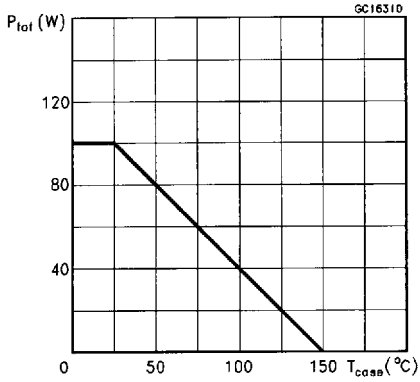
Thermal Impedeance For TO-220



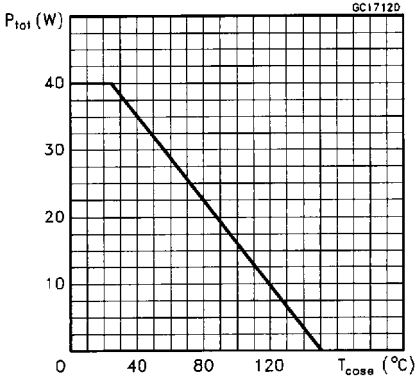
Thermal Impedance For ISOWATT220



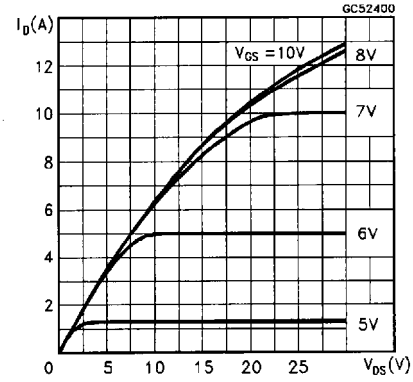
Derating Curve For TO-220



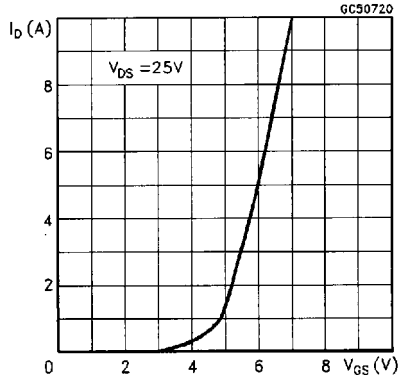
Derating Curve For ISOWATT220



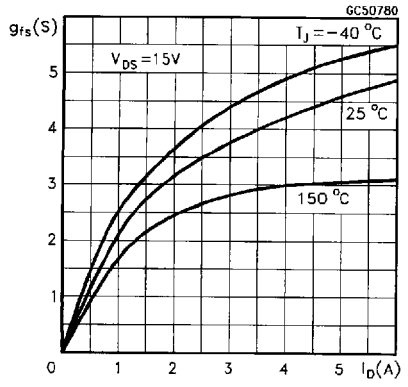
Output Characteristics



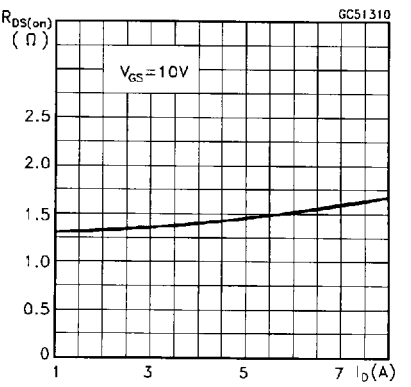
Transfer Characteristics



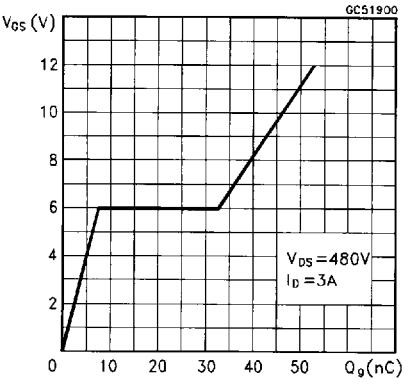
Transconductance



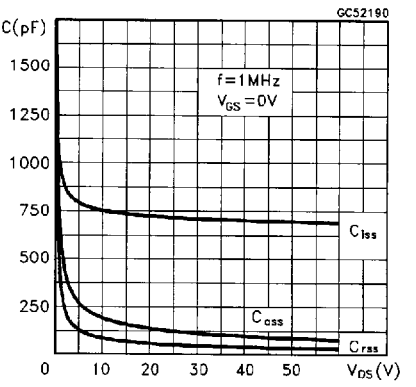
Static Drain-source On Resistance



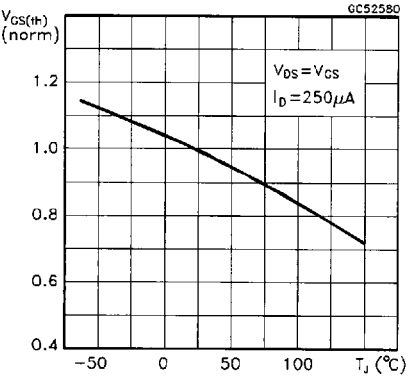
Gate Charge vs Gate-source Voltage



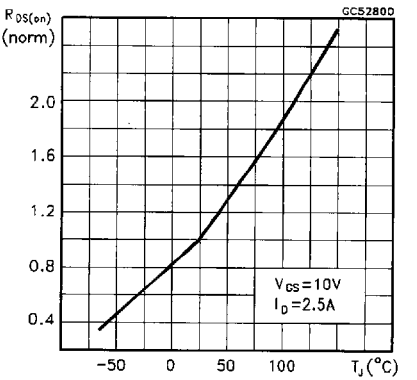
Capacitance Variations



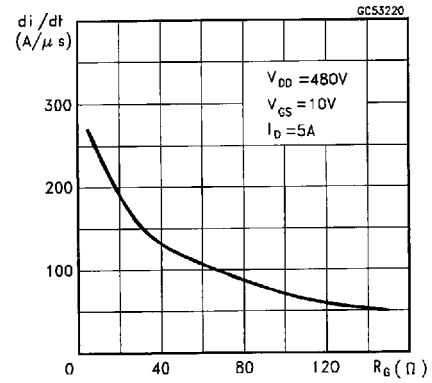
Normalized Gate Threshold Voltage vs Temperature



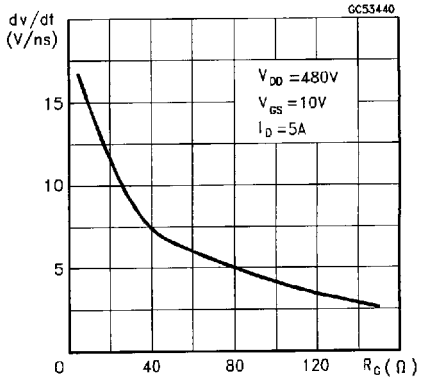
Normalized On Resistance vs Temperature



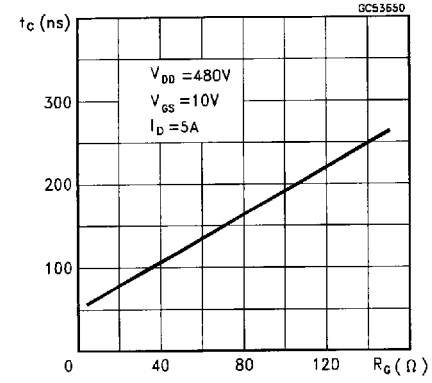
Turn-on Current Slope



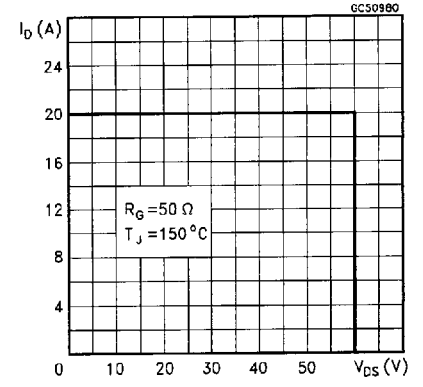
Turn-off Drain-source Voltage Slope



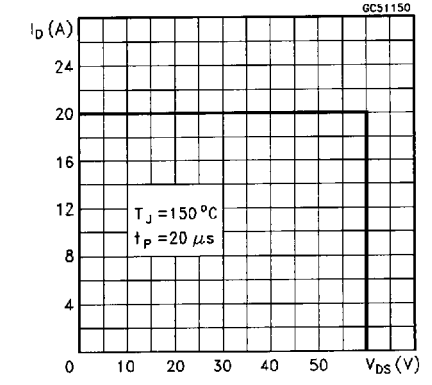
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

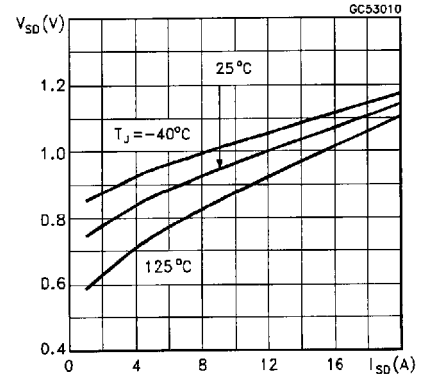


Fig. 1: Unclamped Inductive Load Test Circuits

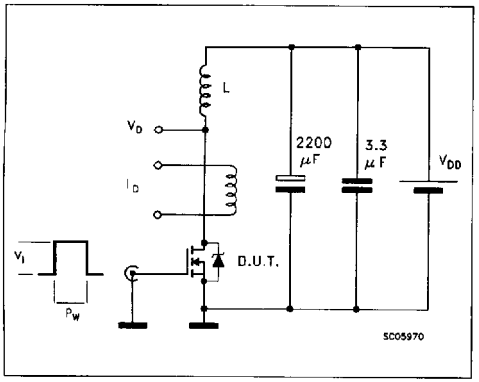


Fig. 2: Unclamped Inductive Waveforms

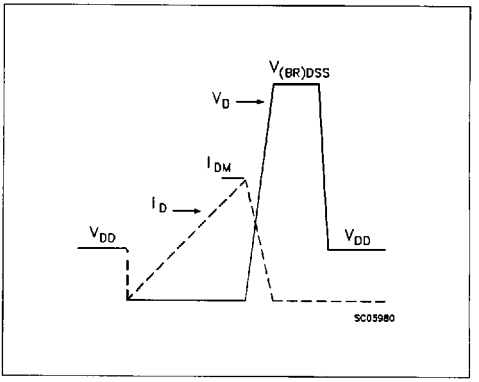


Fig. 3: Switching Times Test Circuits For Resistive Load

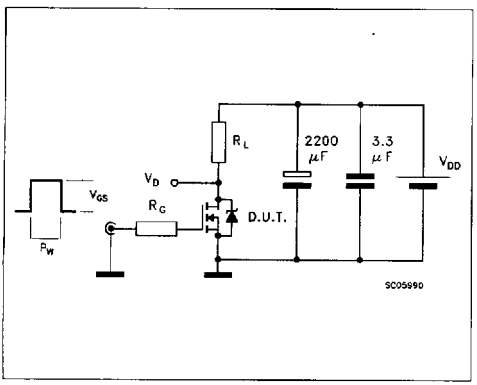


Fig. 4: Gate Charge Test Circuit

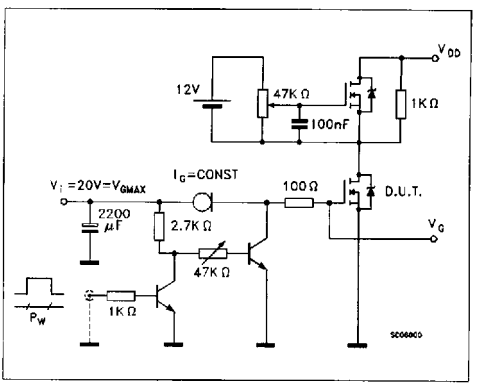


Fig. 5: Test Circuit For Inductive Load Switching And Diode Reverse Recovery Time

